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(54) METHODS FOR PRODUCING LOW STRESS POROUS LOW-K DIELECTRIC MATERIALS USING PRECURSORS WITH ORGANIC FUNCTIONAL GROUPS

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Subject to any disclaimer, the term of this Notice: patent is extended or adjusted under 35 U.S.C. 154(b) by 113 days.

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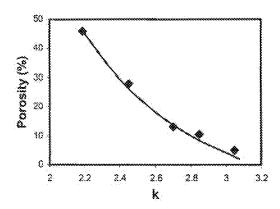
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- (63) Continuation-in-part of application No. 10/672,311, filed on Sep. 26, 2003, which is a continuation-in-part of application No. 10/404,693, filed on Mar. 31, 2003.
- (51) Int. CL H011, 21/31 (2006.01)H01L 21/469 (2006.01) C23C 16/40 (2006.01)(2006.01)C23C 16/56
- 438/781, 438/789, 438/790; (52) U.S. CL
- 427/255.18, 225.27, 255.37, 255.393.387. 427/551, 553, 557, 438/507, 509, 780-782, 438/787, 788, 789, 790, 783, 784 See application file for complete search history.

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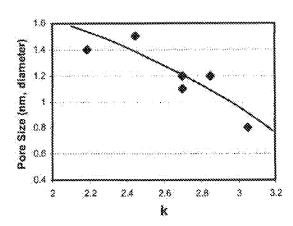
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Primary Examiner - M. Wilczewski (74) Attorney, Agent, or Firm-Beyer Weaver LLP

ABSTRACT

Methods of preparing a low stress porous low-k dielectric material on a substrate are provided. The methods involve the use of a simultone former precursor and/or porogen precursor with one or more organic functional groups. In some cases, the structure former precursor has carboncarbon double or triple bonds. In other cases, one or both of the structure former precursor and porogen precursor has one or more bulky organic groups. In other cases, the structure former precursor has carbon-carbon double or triple bonds and one or both of the structure former precursor and porogen precursor has one or more bulky organic groups. Once the precursor film is formed, the porogen is removed, leaving a porous low-k dielectric matrix with high mechanical strength. Different types of structure former precursors and porogen precursors are described. The resulting low stress low-k porous film may be used as a low-k dielectric film in integrated circuit manufacturing applications.

30 Claims, 7 Drawing Sheets





(19) United States

(12) Patent Application Publication (10) Pub. No.: US 2007/0093078 A1 Harada et al. (43) Pub. Date:

Apr. 26, 2007

(54) POROUS INSULATING FILM, METHOD FOR PRODUCING THE SAME, AND SEMICONDUCTOR DEVICE USING THE SAME

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(21) Appl. No.: 10/580,606

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> § 371(c)(1), May 25, 2006 (2), (4) Date:

(30)Foreign Application Priority Data

Nov. 28, 2003 (JP) ______ 2003-400683

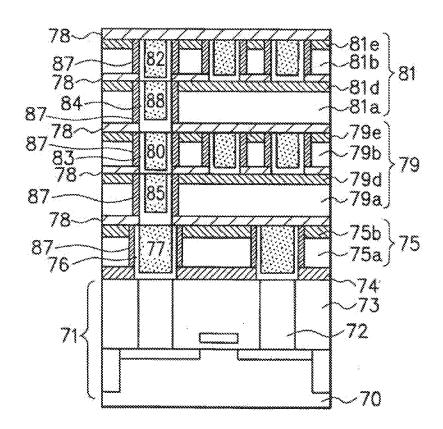
Publication Classification

(51) Int. Cl. H01L 21/31 (2006.01)H01L 21/469 (2006.01)

U.S. CL 438/790

(57)ABSTRACT

The present invention provides a process of producing a porous insulating film effective as an insulating film constituting a semiconductor device and a process of producing a porous insulating film having high adhesion to a semiconductor material, which is in contact with the upper and lower interfaces of the insulating film. Gas containing molecule vapor of at least one or more organic silica compounds, which have a cyclic silica skeleton in its molecule and have at least one or more unsaturated hydrocarbon groups bound with the cyclic silies skeleton is introduced into plasma to grow a porous insulating film on a semiconductor substrate.





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